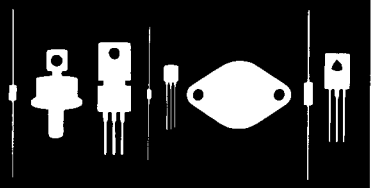
Central
Semiconductor Corp.
145 Adams Avenue
Hauppauge, New York 11788



2N4036
2N4037

SILICON PNP TRANSISTOR

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N4036, 2N4037 are Silicon PNP Epitaxial Planar Transistors designed for small signal and medium power general purpose industrial applications.

MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

	SYMBOL	2N4036	2N4037	UNIT
Collector-Base Voltage	V_{CBO}	90	60	V
Emitter-Base Voltage	V_{EBO}	7.0	7.0	V
Collector-Emitter Voltage	V_{CEO}	65	40	V
Collector-Emitter Voltage	V_{CEV}, V_{CER}	85	60	V
Collector Current, Continuous	I_C	1.0	1.0	A
Base Current	I_B	0.5	0.5	A
Power Dissipation	P_D	7.0	7.0	W
Power Dissipation (T_A=25°C)	P_D	1.0	1.0	W
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 TO +200		°C

ELECTRICAL CHARACTERISTICS (T_C=25°C)

SYMBOL	TEST CONDITIONS	2N4036 MIN	2N4036 MAX	2N4037 MIN	2N4037 MAX	UNIT
I_{CBO}	V_{CB}=60V		0.02		0.25	uA
I_{EBO}	V_{EB}=5V		0.02		1.0	uA
I_{CEO}	V_{CE}=30V		0.5		5.0	uA
BV_{CBO}	I_C=0.1mA	90		60		V
BV_{EBO}	I_E=0.1mA	7.0		7.0		V
BVCEO	I_C=100mA	65		40		V
BV_{CER}	I_C=100mA, R_{BE}=200 OHMS	85		60		V
BV_{CEV}	V_{BE}=1.5V, I_C=100mA	85		60		V
$V_{CE(s)}$	I_C=150mA, I_B=15mA		0.65		1.4	V
$V_{BE(on)}$	V_{CE}=10V, I_C=150mA		1.1		1.5	V
h_{FE}	V_{CE}=10V, I_C=0.1mA	20		--		--
h_{FE}	V_{CE}=10V, I_C=1.0mA	--		15		--
h_{FE}	V_{CE}=10V, I_C=150mA	40	140	50	250	--
h_{FE}	V_{CE}=10V, I_C=500mA	20		--		--
f_T	V_{CE}=10V, I_C=50mA, f=20 MHz	60		60		MHz
C_{ob}	V_{CB}=10V, I_E=0		30		30	pF
t_{on}	V_{CE}=30V, I_C=150mA, I_{B1}=15mA		110		--	nSEC
t_{off}	V_{CE}=30V, I_C=150mA, I_{B2}=15mA		700		--	nSEC

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824